

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Kazumasa HIRAMATSU et al. Conf.: 5987
Appl. No.: 09/522,701 Group: 2815
Filed: March 10, 2000 Examiner: B. Baumeister
For: III-V COMPOUND SEMICONDUCTOR

REPLY UNDER 37 C.F.R. § 1.116

Assistant Commissioner for Patents
Washington, DC 20231

January 24, 2003

Sir:

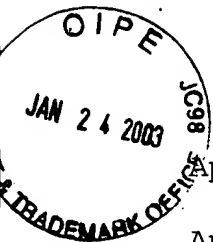
In response to the Office Action of July 24, 2002, the period for response having been extended three months, the following amendments and remarks are submitted in connection with the above-identified application.

AMENDMENTS

IN THE CLAIMS:

Please amend the claims as follows:

D' 1. (Twice Amended) A III-V compound semiconductor having a first layer that comprises a first III-V compound semiconductor expressed by the general formula $\text{In}_u\text{Ga}_v\text{Al}_w\text{N}$ where $0 \leq u \leq 1$, $0 \leq v \leq 1$, $0 \leq w \leq 1$, and $u+v+w=1$, a pattern on said first layer from a material different not only from said first III-V compound semiconductor but also from a second III-V compound



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And
HFE
J. McMillan
1/31/03
entered
JAN 29 2003
RECEIVED
TECHNOLOGY CENTER 8800
2/12/03